

## Descriptions

- Switching application
- Interface circuit and driver circuit application

## Features

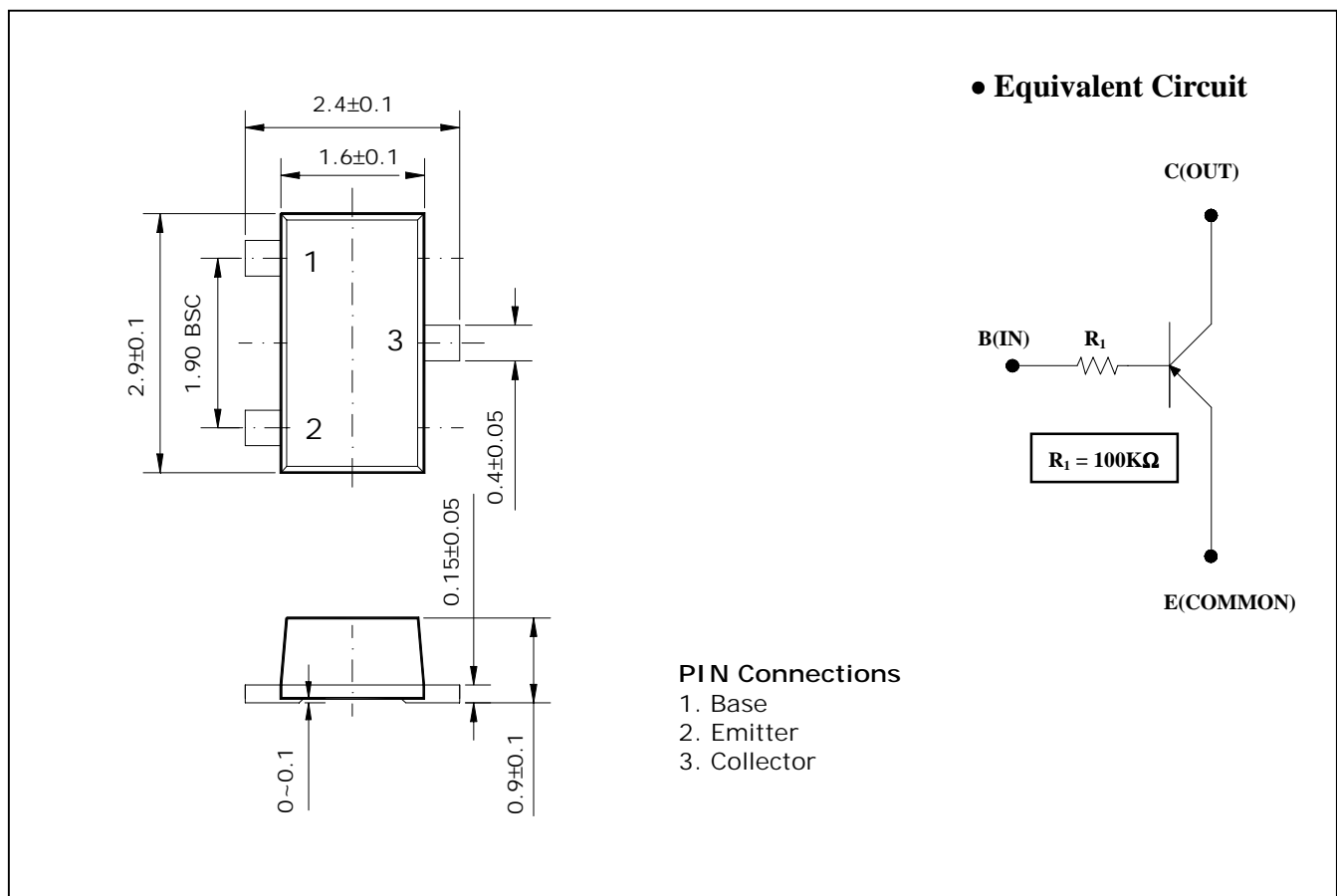
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- High packing density

## Ordering Information

Type NO.	Marking	Package Code
SRA2212SF	RAB	SOT-23F

## Outline Dimensions

unit : mm



**Absolute maximum ratings**

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-100	mA
Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{STG}$	-55 ~ 150	°C

**Electrical Characteristics**

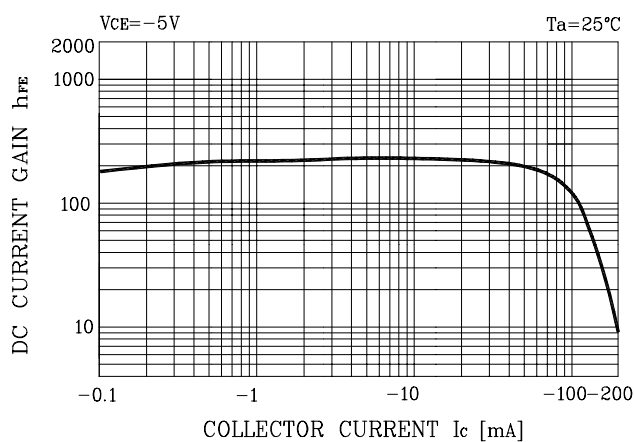
(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$	-	-	-500	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	-	-	-500	nA
DC Current Gain	$h_{FE}$	$V_{CE} = -5V, I_C = -1mA$	120	-	-	-
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -10mA, I_B = -0.5mA$	-	-0.1	-0.3	V
Transition Frequency	$f_T^*$	$V_{CE} = -10V, I_C = -5mA$	-	250	-	MHz
Input Resistance	$R_1$	-	-	100	-	KΩ

\* : Characteristic of Transistor Only

**Electrical Characteristic Curves**

**Fig. 1  $h_{FE} - I_C$**



**Fig. 2  $V_{CE(SAT)} - I_C$**

